

November 2013

FDB031N08

N-Channel PowerTrench[®] MOSFET 75 V, 235 A, 3.1 m Ω

Features

- $R_{DS(on)}$ = 2.4 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 75 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{DS(\text{on})}$
- · High Power and Current Handling Capability
- RoHS Compliant

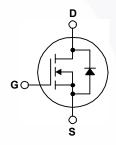
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- · Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FDB031N08	Unit
V_{DSS}	Drain to Source Voltage			75	V
V_{GSS}	Gate to Source Voltage			±20	V
	Drain Current -	Continuous (T _C = 25°C, Silico	n Limited)	235	Α
I _D		Continuous (T _C = 100°C, Silico	n Limited)	165	Α
	- Continuous (T _C = 25°C, Package Limited)			120	Α
I _{DM}	Drain Current	- Pulsed	(Note 1)	940	Α
E _{AS}	Single Pulsed Avalanche E	Single Pulsed Avalanche Energy (Note 2)			mJ
dv/dt	Peak Diode Recovery dv/d	t	(Note 3)	5.5	V/ns
D	Dower Dissipation	(T _C = 25°C)		375	W
P _D Power Dissipation		- Derate Above 25°C		2.5	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +175	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	οС

Thermal Characteristics

Symbol	Parameter	FDB031N08	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. 62.5		C/VV

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDB031N08	FDB031N08	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_C = 25^{\circ}C$	75	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	-	0.05	-	V/°C
1	Zero Gate Voltage Drain Current	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	
IDSS	Zero Gate voltage Drain Current	$V_{DS} = 75 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μΑ
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	2.5	3.5	4.5	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 75 A	-	2.4	3.1	mΩ
9 _{FS}	Forward Transconductance	V _{DS} = 10 V, I _D = 75 A	-	180	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 05 V V 0 V	-	11400	15160	pF
Coss	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$	-	1360	1810	pF
C _{rss}	Reverse Transfer Capacitance	1 = 1 WHZ	-	595	800	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 60 V, I _D = 75 A,	-	169	220	nC
Q _{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	60	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note	4) _	47	-	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	230	470	ns
t _r		$V_{DD} = 37.5 \text{ V}, I_D = 75 \text{ A},$	-	191	392	ns
t _{d(off)}	Turn-Off Delay Time	$R_G = 25 \Omega, V_{GS} = 10 V$	-	335	680	ns
t _f	Turn-Off Fall Time	(Note 4)	-	121	252	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	235	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	940	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 75 A	-	-	1.3	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 75 A,	-	53	-	ns
Q_{rr}	Reverse Recovery Charge	dI _F /dt = 100 A/μs	-	77	_	nC

Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 0.71 mH, I $_{AS}$ = 75 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 $\Omega,$ starting T $_{J}$ = 25 $^{\circ}C.$
- 3. I $_{SD}$ \leq 75 A, di/dt \leq 200 A/µs, V $_{DD}$ \leq BV $_{DSS}$, starting T $_{J}$ = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

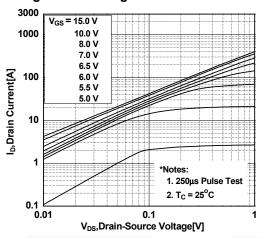


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

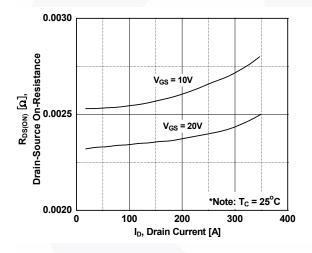


Figure 5. Capacitance Characteristics

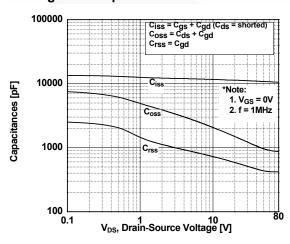


Figure 2. Transfer Characteristics

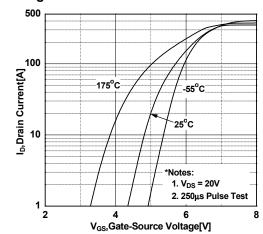


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

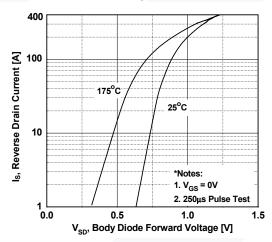
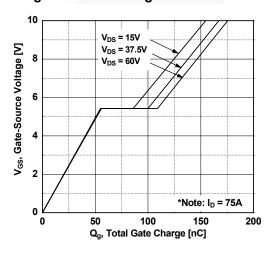


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

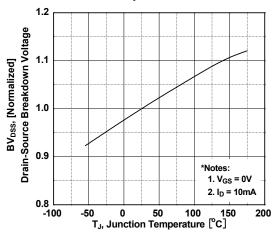


Figure 8. On-Resistance Variation vs. Temperature

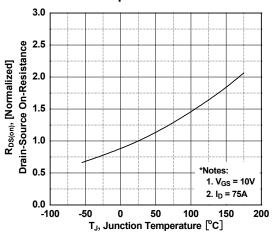
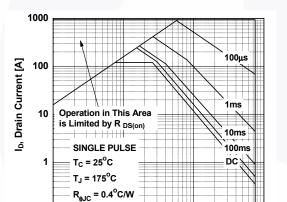


Figure 9. Maximum Safe Operating Area



V_{DS}, Drain-Source Voltage [V]

Figure 10. Maximum Drain Current vs. Case Temperature

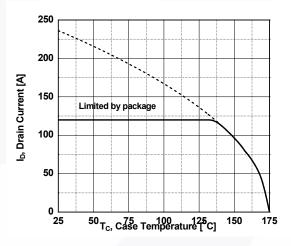
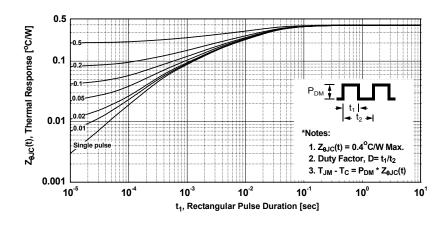


Figure 11. Transient Thermal Response Curve

100



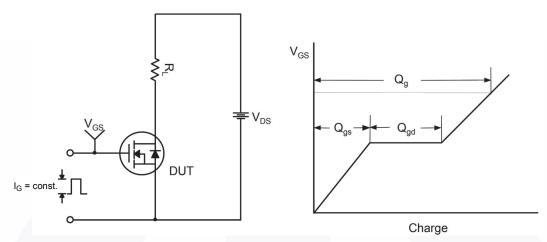


Figure 12. Gate Charge Test Circuit & Waveform

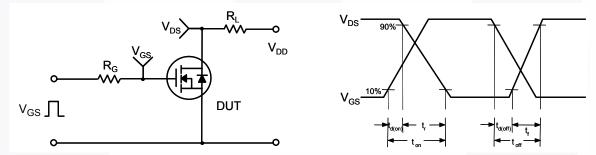


Figure 13. Resistive Switching Test Circuit & Waveforms

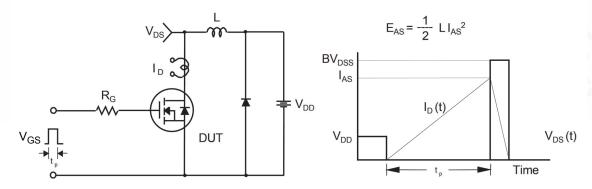


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

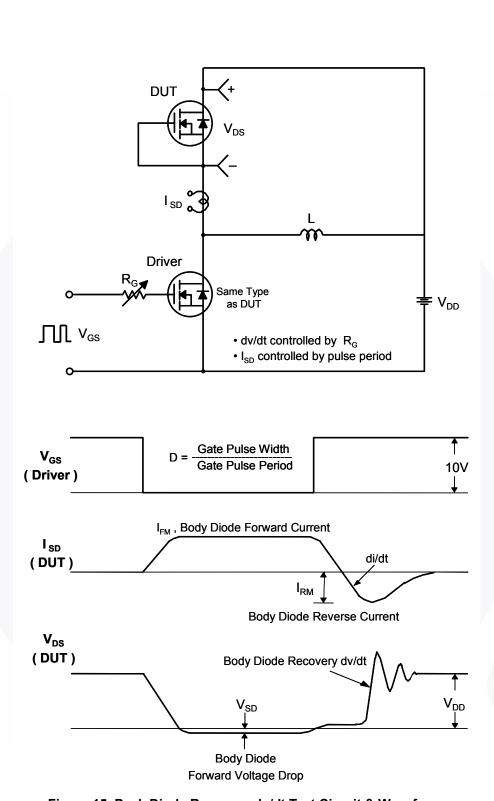


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

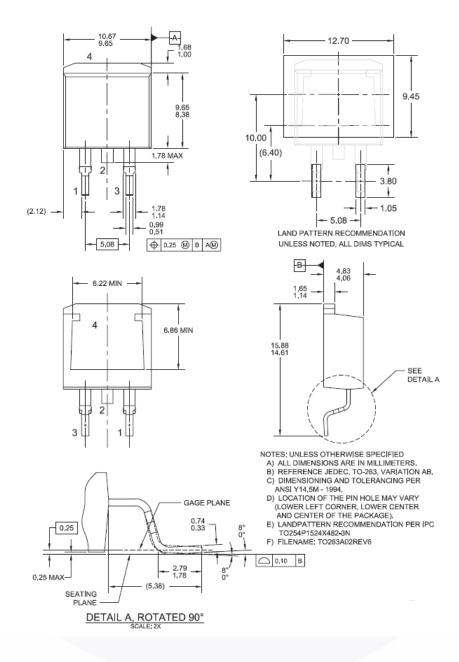


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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